

isc Silicon PNP Power Transistor

2SB1096

DESCRIPTION

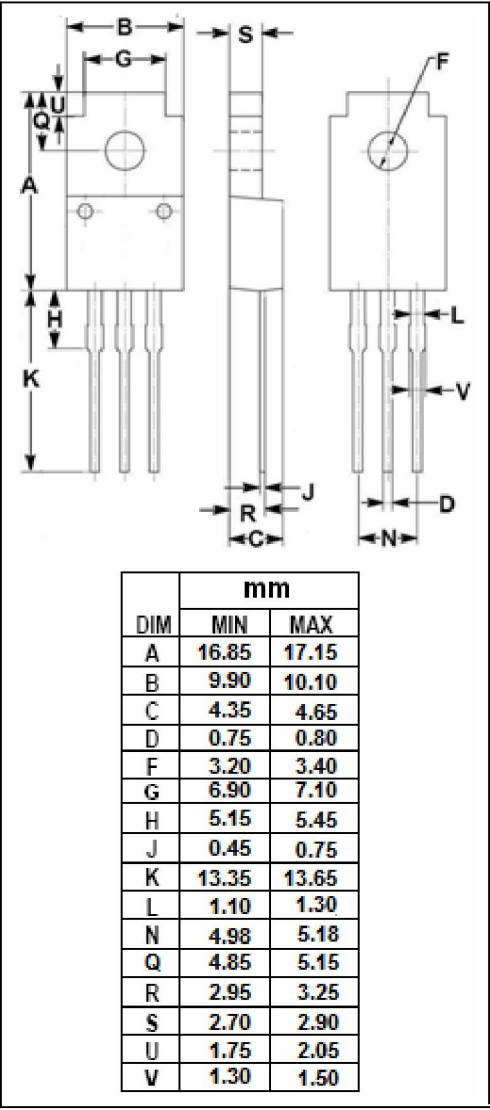
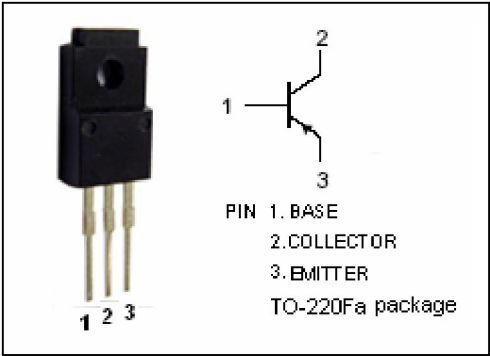
- High Collector Current:: $I_C = -2A$
- Good Linearity of h_{FE}
- Complement to Type 2SD1587

APPLICATIONS

- Designed for color TV vertical deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Pulse	-3	A
I_B	Base Current-Continuous	-1.0	A
P_C	Total Power Dissipation @ $T_a=25^{\circ}C$	2	W
	Total Power Dissipation @ $T_C=25^{\circ}C$	25	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SB1096****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -0.5\text{A}; I_B = -50\text{mA}$			-1.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -150\text{V}; I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-50	μA
h_{FE}	DC Current Gain	$I_C = -0.4\text{A}; V_{CE} = -10\text{V}$	40		200	
f_T	Current-Gain—Bandwidth Product	$I_C = -0.4\text{A}; V_{CE} = -10\text{V}$		5		MHz

◆ **h_{FE} Classifications**

M	L	K
40-80	60-120	100-200